

## Features

- Dual P-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage  $V_{GS(TH)} < 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **ESD Protected Gate**
- **"Green" Device (Note 3)**

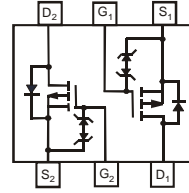


TOP VIEW



BOTTOM VIEW

SOT-563


 TOP VIEW  
Internal Schematic

## Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)

## Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 8$	V
Continuous Drain Current (Note 1)	$I_D$	-530	mA
Pulsed Drain Current	$I_{DM}$	1.8	A

## Thermal Characteristics @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	$P_d$	400	mW
Thermal Resistance, Junction to Ambient, Note 1	$R_{\theta JA}$	312.5	$^\circ C/W$
Operating and Storage Temperature Range	$T_j, T_{STG}$	-65 to +150	$^\circ C$

## Electrical Characteristics @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	-20	—	—	V	$V_{GS} = 0V, I_D = -250mA$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	-1.0	$\mu A$	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 1.0$	$\mu A$	$V_{GS} = \pm 4.5V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 4)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	—	-1.0	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	0.7	0.9	$\Omega$	$V_{GS} = -4.5V, I_D = -430mA$
			1.1	1.4		$V_{GS} = -2.5V, I_D = -300mA$
			1.7	2.0		$V_{GS} = -1.8V, I_D = -150mA$
Forward Transfer Admittance	$ Y_{fs} $	200	—	—	mS	$V_{DS} = -10V, I_D = -0.2A$
Diode Forward Voltage (Note 4)	$V_{SD}$	-0.5	—	-1.2	V	$V_{GS} = 0V, I_S = 115mA$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{iss}$	—	—	175	pF	$V_{DS} = -16V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	—	30	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	—	20	pF	

- Notes:
1. Device mounted on FR-4 PCB.
  2. No purposefully added lead.
  3. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  4. Short duration pulse test used to minimize self-heating effect.

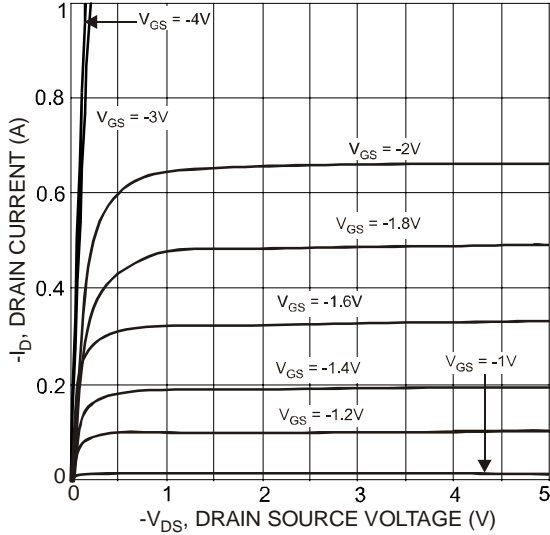


Fig. 1 Typical Output Characteristics

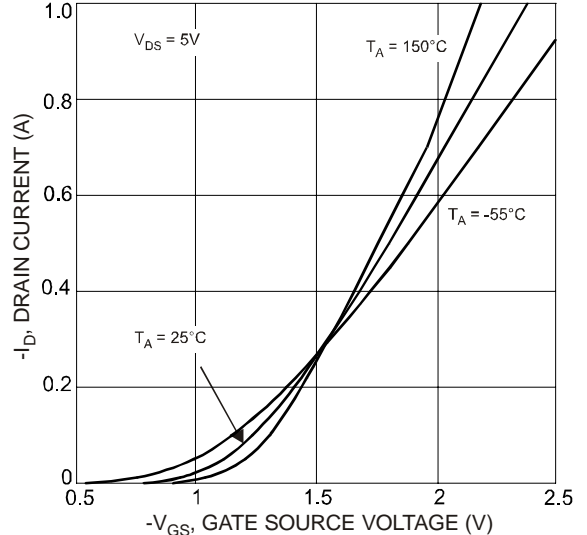


Fig. 2 Typical Transfer Characteristics

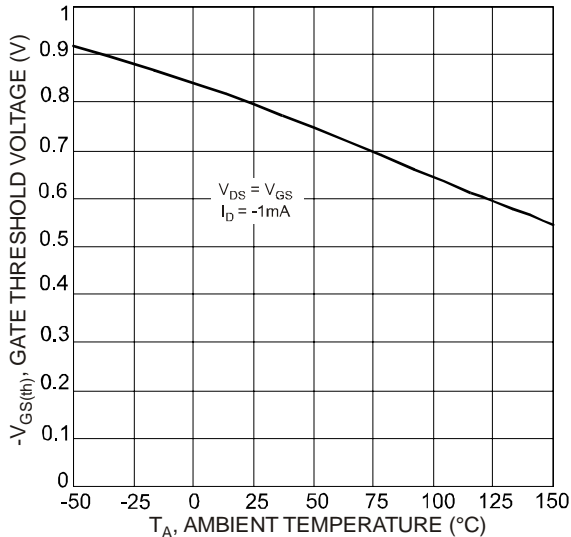


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

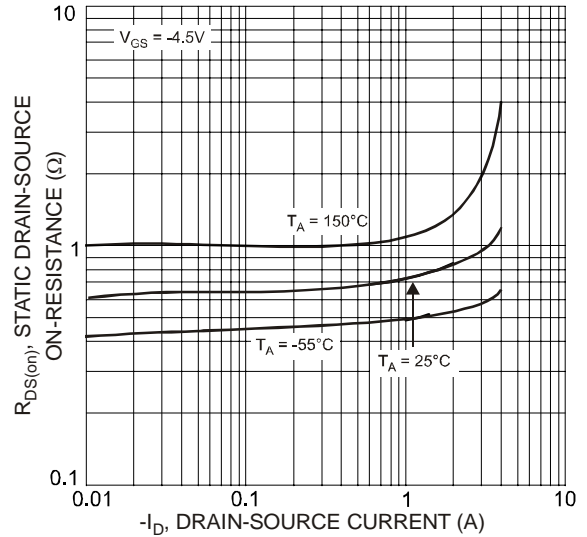


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

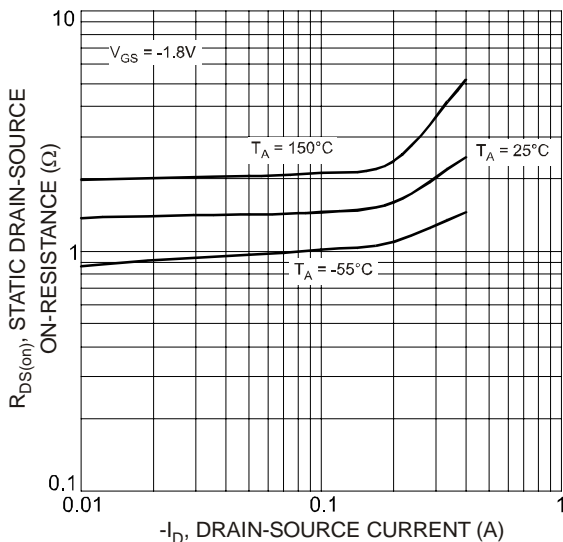


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

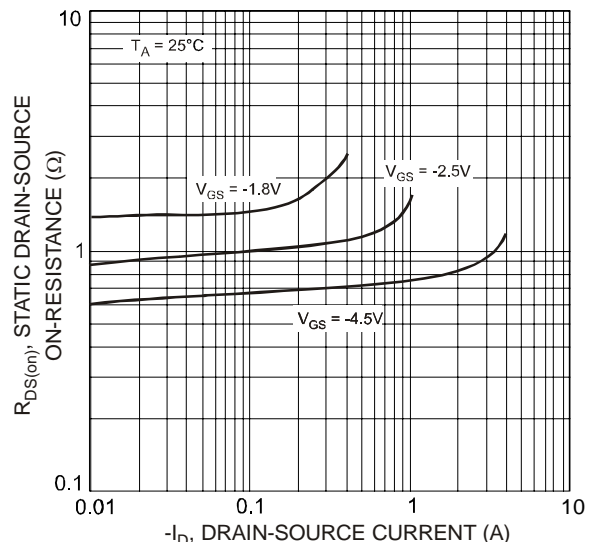


Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current

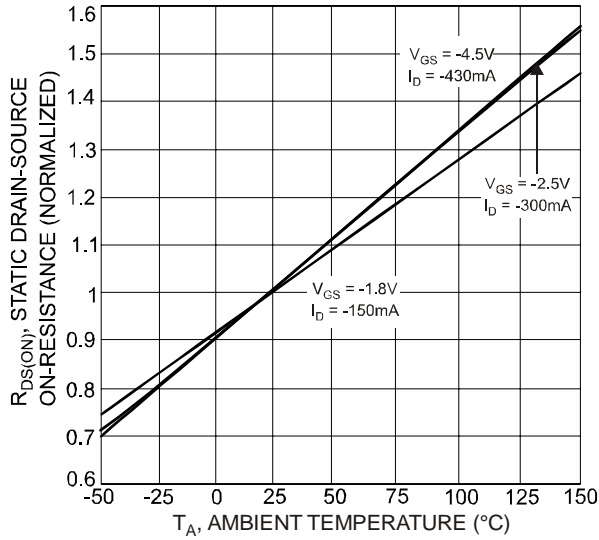


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

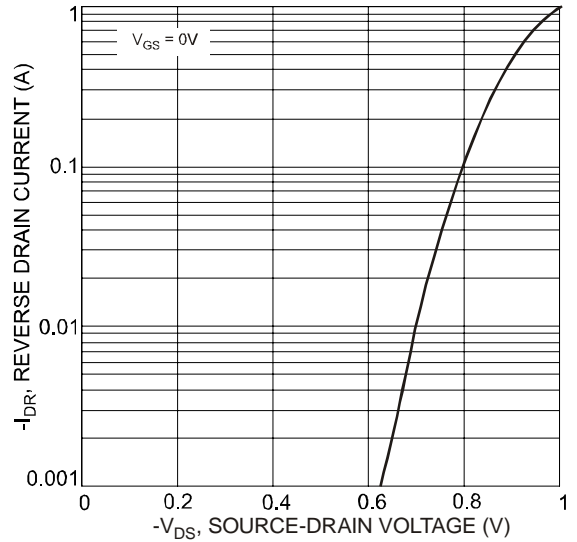


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

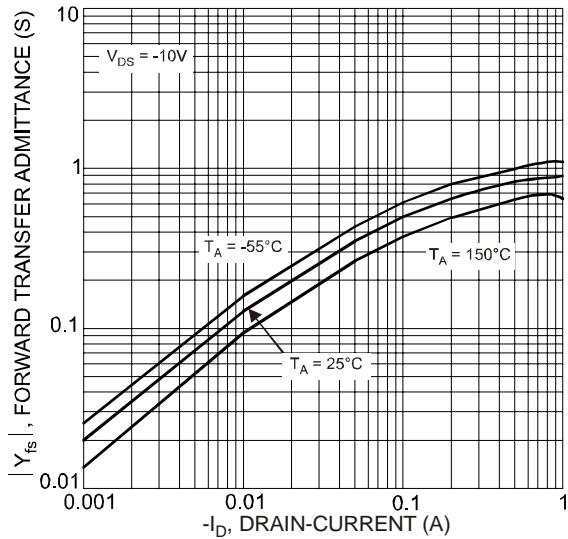


Fig. 9 Forward Transfer Admittance vs. Drain-Current

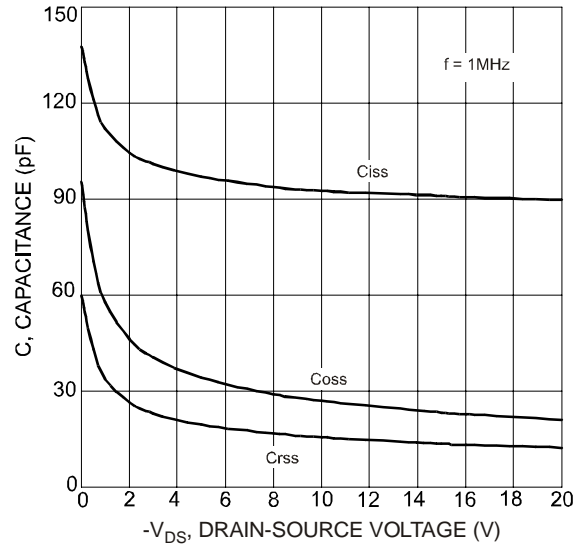


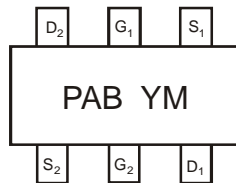
Fig. 10 Typical Capacitance

**Ordering Information** (Note 5)

Part Number	Case	Packaging
DMP2004VK-7	SOT-563	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**

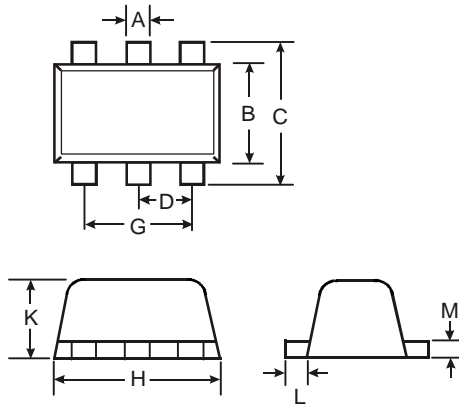


PAB = Marking Code  
YM = Date Code Marking  
Y = Year ex: U = 2007  
M = Month ex: 9 = September

Date Code Key

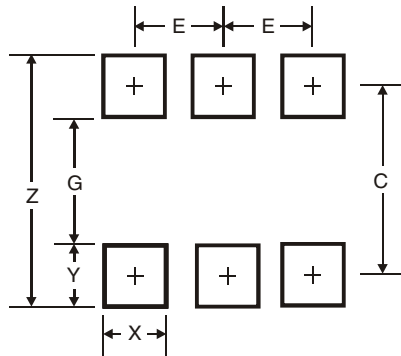
Year	2007	2008	2009	2010	2011	2012						
Code	U	V	W	X	Y	Z						
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Package Outline Dimensions**



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

**Suggested Pad Layout**



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C	1.7
E	0.5

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